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30V, N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD17327Q5A

FEATURES

- Ultralow Q_g and Q_{gd}
- · Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

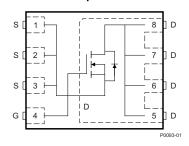
APPLICATIONS

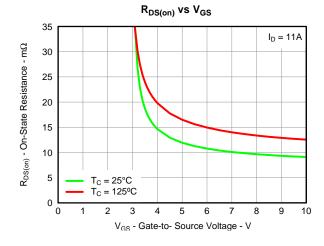
- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems
- Optimized for Control FET Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.







PRODUCT SUMMARY

V _{DS}	Drain to Source Voltage	30	V	
Q_g	Gate Charge Total (4.5V)	2.8	nC	
Q_{gd}	Gate Charge Gate to Drain	0.8	nC	
В	Drain to Source On Resistance	$V_{GS} = 4.5V$	12.5	mΩ
R _{DS(on)}	Diam to Source On Resistance	$V_{GS} = 8V$	9.9	mΩ
V _{GS(th)}	Threshold Voltage	1.6	V	

ORDERING INFORMATION

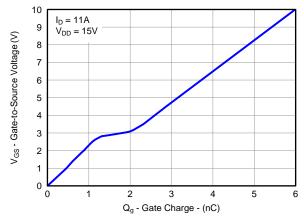
Device	Device Package		Qty	Ship	
CSD17327Q5A	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel	

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	+10 / -10	٧
	Continuous Drain Current, T _C = 25°C	65	Α
I _D	Continuous Drain Current ⁽¹⁾	13	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	85	Α
P_D	Power Dissipation ⁽¹⁾	3	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse I_D = 30A, L = 0.1mH, R_G = 25 Ω	45	mJ

- (1) Typical $R_{\rm BJA}=44^{\circ}{\rm C/W}$ on 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.
- (2) Pulse duration ≤300µs, duty cycle ≤2%

GATE CHARGE



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
haracteristics	·				
Drain to Source Voltage	$V_{GS} = 0V, I_{DS} = 250\mu A$	30			V
Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 24V			1	μA
Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = +10/-10V			100	nA
Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250 \mu A$	1.1	1.6	2.0	V
Dunin to Course On Boninton	V _{GS} = 4.5V, I _{DS} = 11A		12.5	15.5	mΩ
Drain to Source On Resistance	V _{GS} = 8V, I _{DS} = 11A		9.9	12.2	mΩ
Transconductance	V _{DS} = 15V, I _{DS} = 11A		44		S
Characteristics					
Input Capacitance		422		506	pF
Output Capacitance			286	343	pF
Reverse Transfer Capacitance	1 - 10112		26	33	pF
Series Gate Resistance			4.7		Ω
Gate Charge Total (4.5V)			2.8	3.4	nC
Gate Charge Gate to Drain	V 45V L 44A		0.8		nC
Gate Charge Gate to Source	V _{DS} = 15V, I _{DS} = 11A		1.2		nC
Gate Charge at Vth			0.6		nC
Output Charge	$V_{DS} = 13V, V_{GS} = 0V$		6.8		nC
Turn On Delay Time			5.6		ns
Rise Time	$V_{DS} = 15V, V_{GS} = 4.5V,$		8.2		ns
Turn Off Delay Time	$I_{DS} = 11A, R_G = 2\Omega$		9.8		ns
Fall Time			3.2		ns
haracteristics		•			
Diode Forward Voltage	I _{SD} = 11A, V _{GS} = 0V		0.85	1	V
Reverse Recovery Charge	V 40V L 44A 4:/4k 2004/		10.5		nC
Reverse Recovery Time	$v_{DS} = 13V$, $I_F = 11A$, $\alpha I/\alpha t = 300A/\mu s$		14.6		ns
	Drain to Source Voltage Drain to Source Leakage Current Gate to Source Leakage Current Gate to Source Threshold Voltage Drain to Source On Resistance Transconductance Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance Series Gate Resistance Gate Charge Total (4.5V) Gate Charge Gate to Drain Gate Charge Gate to Source Gate Charge at Vth Output Charge Turn On Delay Time Rise Time Turn Off Delay Time Fall Time Diode Forward Voltage Reverse Recovery Charge	naracteristics Drain to Source Voltage $V_{GS} = 0V$, $I_{DS} = 250\mu A$ Drain to Source Leakage Current $V_{GS} = 0V$, $V_{DS} = 24V$ Gate to Source Leakage Current $V_{DS} = 0V$, $V_{GS} = +10/-10V$ Gate to Source Threshold Voltage $V_{DS} = 0V$, $V_{GS} = 250\mu A$ Drain to Source On Resistance $V_{DS} = V_{DS}$, $I_{DS} = 250\mu A$ Drain to Source On Resistance $V_{CS} = 8V$, $V_{DS} = 11A$ Transconductance $V_{DS} = 15V$, $V_{DS} = 11A$ Characteristics Input Capacitance Output Capacitance $V_{CS} = 0V$, $V_{DS} = 15V$, $V_{CS} = $	naracteristics Drain to Source Voltage V _{GS} = 0V, I _{DS} = 250µA 30 Drain to Source Leakage Current V _{GS} = 0V, V _{DS} = 24V Gate to Source Threshold Voltage V _{DS} = 0V, V _{GS} = +10/-10V Gate to Source Threshold Voltage V _{DS} = V _{GS} , I _{DS} = 250µA 1.1 Drain to Source On Resistance V _{GS} = 4.5V, I _{DS} = 11A 1.1 Transconductance V _{DS} = 15V, I _{DS} = 11A 1.1 **Characteristics** Input Capacitance V _{GS} = 0V, V _{DS} = 15V, I _{DS} = 15V, I _{DS} = 11A **Characteristics** V _{GS} = 0V, V _{DS} = 15V, I _{DS} = 11A **Gate Charge Gate to Drain V _{DS} = 15V, I _{DS} = 0V **Gate Charge Gate to Source V _{DS} = 13V, V _{GS} = 0V **Gate Charge at Vth V _{DS} = 13V, V _{GS} = 0V **Output Charge V _{DS} = 15V, V _{GS} = 4.5V, I _{DS} = 11A **Charge Time V _{DS} = 15V, V _{GS} = 0V **Turn Off Delay Time I _{DS} = 11A, R _G = 2Ω **Fall Time I _{DS} = 11A, V _{GS} = 0V **Parameteristics I _D = 11A, I _D	Drain to Source Voltage V _{GS} = 0V, I _{DS} = 250μA 30 Drain to Source Leakage Current V _{GS} = 0V, V _{DS} = 24V Gate to Source Leakage Current V _{DS} = 0V, V _{GS} = +10/-10V Gate to Source Threshold Voltage V _{DS} = V _{GS} , I _{DS} = 250μA 1.1 1.6 Drain to Source On Resistance V _{GS} = 4.5V, I _{DS} = 11A 12.5 Drain to Source On Resistance V _{GS} = 8V, I _{DS} = 11A 9.9 Transconductance V _{DS} = 15V, I _{DS} = 11A 44 Characteristics 422 422 Input Capacitance 422 422 Output Capacitance 422 286 Reverse Transfer Capacitance 4.7 286 Series Gate Resistance 4.7 2.8 Gate Charge Total (4.5V) 2.8 0.8 Gate Charge Gate to Drain 0.8 0.8 Gate Charge at Vth 0.6 0.6 Output Charge V _{DS} = 13V, V _{GS} = 0V 6.8 Turn On Delay Time 5.6 Rise Time V _{DS} = 15V, V _{GS} = 4.5V, I _{DS} = 11A, R _G = 2Ω 9.8 Fall Time <	Drain to Source Voltage V _{GS} = 0V, I _{DS} = 250μA 30 Drain to Source Leakage Current V _{GS} = 0V, V _{DS} = 24V 1 Gate to Source Leakage Current V _{DS} = 0V, V _{DS} = 24V 100 Gate to Source Threshold Voltage V _{DS} = 0V, V _{DS} = +10/-10V 100 Drain to Source On Resistance V _{DS} = V _{GS} , I _{DS} = 250μA 1.1 1.6 2.0 Drain to Source On Resistance V _{DS} = 15V, I _{DS} = 11A 12.5 15.5 15.5 Transconductance V _{DS} = 15V, I _{DS} = 11A 44 12.2 15.5 Characteristics Input Capacitance 422 506 Output Capacitance V _{DS} = 15V, I _{DS} = 15V, V _{DS} = 15V, from 14V = 15V 286 343 Reverse Transfer Capacitance 4.7 286 343 Reverse Gate Resistance 4.7 286 343 Gate Charge Gate to Drain 0.8 0.8 Gate Charge Gate to Source 0.8 0.8 Gate Charge at Vth 0.6 0.6 Output Charge V _{DS} = 13V, V _{GS} = 0V 6.8 Turn Off Delay Time

THERMAL CHARACTERISTICS

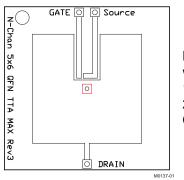
(T_A = 25°C unless otherwise stated)

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾			1.9	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			51	°C/W

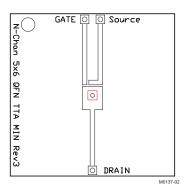
 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.



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Max $R_{\theta JA} = 51^{\circ} C/W$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 131^{\circ} C/W$ when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

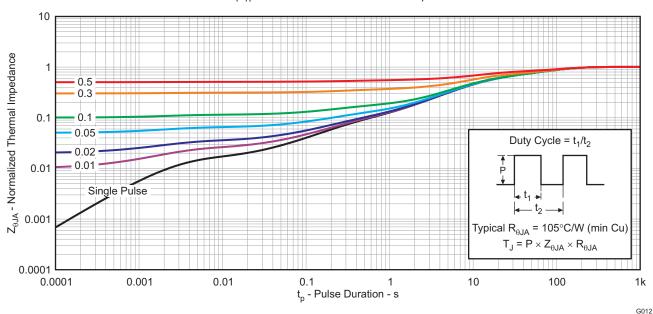


Figure 1. Transient Thermal Impedance

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TEXAS INSTRUMENTS

TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

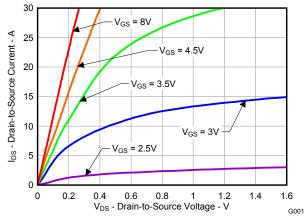


Figure 2. Saturation Characteristics

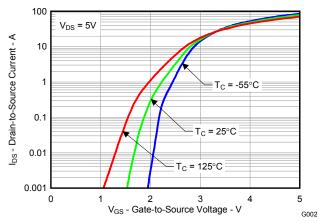


Figure 3. Transfer Characteristics

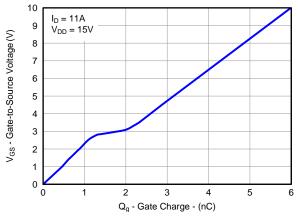


Figure 4. Gate Charge

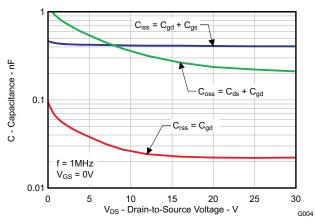


Figure 5. Capacitance

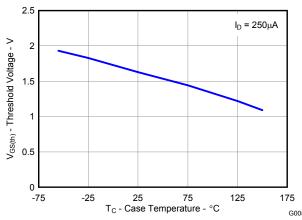


Figure 6. Threshold Voltage vs. Temperature

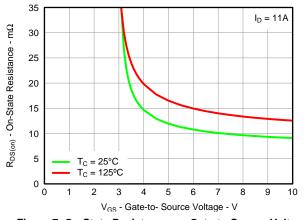


Figure 7. On-State Resistance vs. Gate-to-Source Voltage



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TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

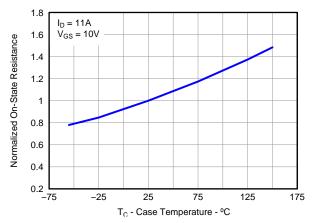


Figure 8. Normalized On-State Resistance vs. Temperature

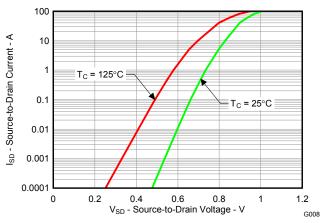


Figure 9. Typical Diode Forward Voltage

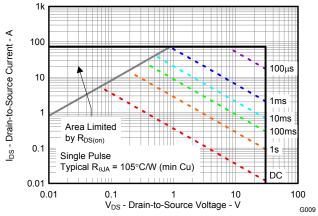


Figure 10. Maximum Safe Operating Area

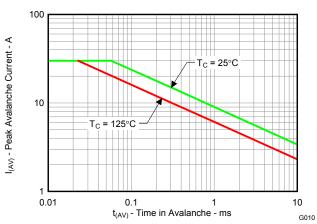
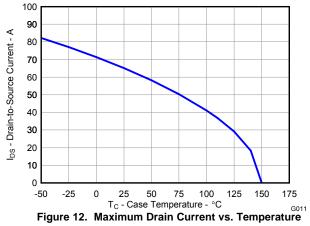


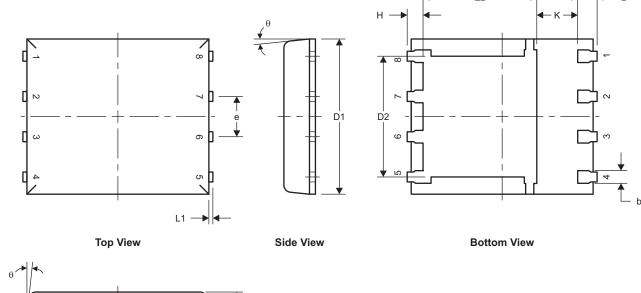
Figure 11. Single Pulse Unclamped Inductive Switching

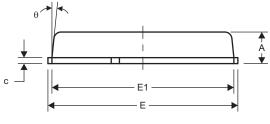




MECHANICAL DATA

Q5A Package Dimensions





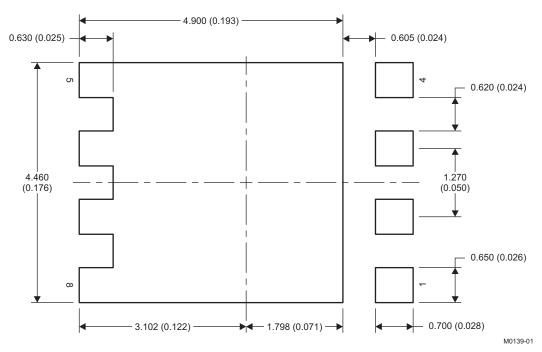
Front View

M0135-01

DIM	MILLIMETERS							
DIM	MIN	NOM	MAX					
Α	0.90	1.00	1.10					
b	0.33	0.41	0.51					
С	0.20	0.25	0.34					
D1	4.80	4.90	5.00					
D2	3.61	3.81	4.02					
E	5.90	6.00	6.10					
E1	5.70	5.75	5.80					
E2	3.38	3.58	3.78					
е	1.17	1.27	1.37					
Н	0.41	0.56	0.71					
K	1.10							
L	0.51	0.61	0.71					
L1	0.06	0.13	0.20					
θ	0°		12°					

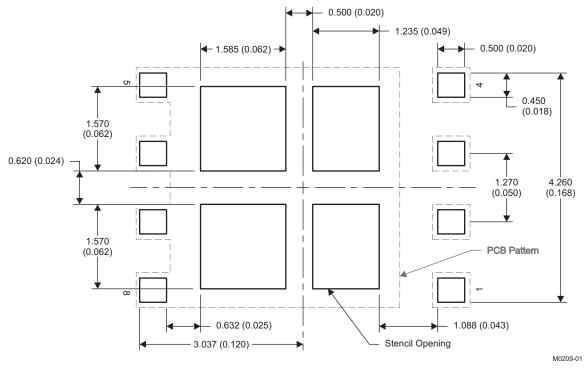
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Recommended PCB Pattern



NOTE: Dimensions are in mm (inches).

Stencil Recommendation



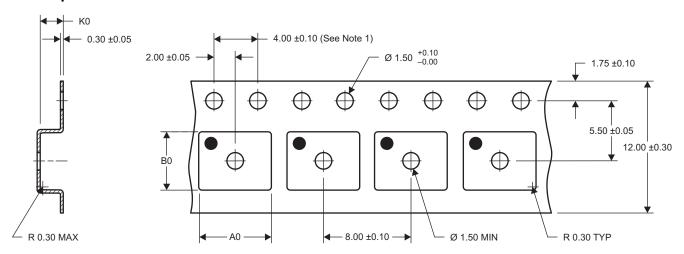
NOTE: Dimensions are in mm (inches).

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

INSTRUMENTS

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Q5A Tape and Reel Information



 $A0 = 6.50 \pm 0.10$ $B0 = 5.30 \pm 0.10$ $K0 = 1.40 \pm 0.10$

M0138-01

- NOTES: 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
 - 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
 - 3. Material: black static-dissipative polystyrene
 - 4. All dimensions are in mm (unless otherwise specified)
 - 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket



PACKAGE OPTION ADDENDUM

22-Aug-2011

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
CSD17327Q5A	ACTIVE	SON	DQJ	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL. Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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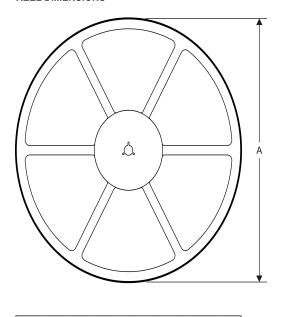
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PACKAGE MATERIALS INFORMATION

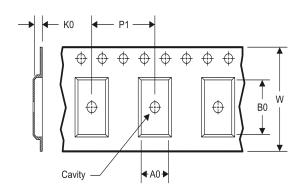
www.ti.com 2-Mar-2012

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD17327Q5A	SON	DQJ	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
I	CSD17327Q5A	SON	DQJ	8	2500	340.0	340.0	38.0	

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